PCN Number:			202	231115001.1			PCN	l Dat	,		
Title:		Qualification of RFAB & DMOS6 as additional Fab site options and Assembly Site (MEX)							d Assembly Site (MEX)		
Title.		and BOM Opt	ions f	for sele	ct	devices					
Custo	mer	Contact:		Chang	je N	lanagement Te	am	Dep	t:		Quality Services
Proposed 1 <sup>st</sup> Ship Date: Feb 1				Feb 13	3, 2	024	Sam acc	ple re cepte			Dec 15, 2023*
*Sam	*Sample requests received after Dec 15, 2023 will not be supported.										
Chan	ge Ty	pe:									
$\boxtimes$	Asse	mbly Site			$\boxtimes$	Design				Waf	fer Bump Material
	Asse	mbly Process				Data Sheet				Waf	fer Bump Process
Assembly Materials					Part number change			⊠   Wa		fer Fab Site	
☐ Mechanical Specification				Test Site			$\boxtimes$	Wafer Fab Material			
☐ Packing/Shipping/Labeling					Test Process			$\boxtimes$	Waf	fer Fab Process	
						PCN Detai	ls				

# **Description of Change:**

Texas Instruments is pleased to announce the qualification of its RFAB & DMOS6 fabrication facilities as an additional Wafer Fab options in addition to Assembly site (MEX) and BOM options for the devices listed below.

С	urrent Fab Site	9	Additional Fab Site				
Current Fab Site	Process	Wafer Diameter	New Fab Site	Process	Wafer Diameter		
DMOS5, CFAB	LBC5	200mm	RFAB, DMOS6	LBC9	300mm		

The die was also changed to support the migration to the LBC9 Process technology

Construction differences are as follows:

	ASESH	FMX
Mount Compound	SID#EY1000063	4224423
Mold Compound	SID#EN2000509	4211880

### Reason for Change:

Supply Continuity

### Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

# **Impact on Environmental Ratings**

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
No Change	☑ No Change	No Change	☑ No Change

### Changes to product identification resulting from this PCN:

### **Fab Site Information:**

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DMOS5	DM5	USA	Dallas
CFAB	CU3	CHN	CHENGDU
RFAB	RFB	USA	Richardson
DMOS6	DM6	USA	Dallas

### Die Rev:

Current New

Die Rev [2P]	Die Rev [2P]
Α	A

# **Assembly Site Information:**

TI Mexico	MEX	MEX	Aguascalientes
ASESH	ASH	CHN	Shanghai
Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City

Sample product shipping label (not actual product label):



MADE IN: Malaysia 2DC: 2Q: MSL 2 /260C/1 YEAR SEAL DT MSL 1 /235C/UNLIM 03/29/04

OPT: ITEM:

5A (L)T0:39750



(1P) \$N74L\$07N\$R (Q) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY(1T) 7523483812

(P) (V) 9933317 (2P) REV: (V) 9933317 (20L) CSO: SHE (21L) CCO:USA (22L) ASO: MLA (23L) ACO: MYS

# **Product Affected:**

DRV8870DDA	DRV8870DDAR	DRV8870LDDAR	SN8870DDAR
BICCOTOBBIC	BICCOTOBBILIC	BITTOOTOLDBITT	CHOO! ODD! III

# **Qualification Report**

# Qualification Plan - DRV8870DDAR PCN bond-out spin at RFAB 2nd source | RFAB-> CD-BP -> FMX (TI Mexico) Approve Date 07-September-2023

#### **Qualification Results**

#### Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Name	Condition	Duration	Qual Device: P2DRV8870DDAR	QBS Reference: <u>TLV62569DBVR</u>	QBS Reference: DRV8251DDAR
HAST	A2	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0
UHAST	A3	Autoclave	121C/15psig	96 Hours	-	3/231/0	3/231/0
TC	A4	Temperature Cycle	-65C/150C	500 Cycles	-	3/231/0	3/231/0
HTSL	A6	High Temperature Storage Life	150C	1000 Hours	-	3/231/0	3/231/0
HTOL	B1	Life Test	125C	1000 Hours	-	3/231/0	1/77/0
ELFR	B2	Early Life Failure Rate	125C	48 Hours	-	3/2400/0	-
SD	СЗ	PB Solderability	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes); PB Solder;	-	-	-	3/66/0
SD	С3	PB-Free Solderability	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes); PB-Free Solder;	-	-	-	3/66/0
ESD	E2	ESD CDM		1500 Volts	-	3/9/0	1/3/0
ESD	E2	ESD HBM	-	2000 Volts	-	3/9/0	-
ESD	E2	ESD HBM	-	4000 Volts	-	-	1/3/0
LU	E4	Latch-Up	Per JESD78	-	-	3/9/0	1/6/0

Туре	#	Test Name	Condition	Duration	Qual Device: P2DRV8870DDAR	QBS Reference: <u>TLV62569DBVR</u>	QBS Reference: DRV8251DDAR
CHAR	E5	Electrical Characterization	Min, Typ, Max Temp	-	1/30/0	3/90/0	3/90/0
CHAR	E5	Electrical Characterization	Per Datasheet Parameters	-	1/30/0	3/90/0	3/90/0

- QBS: Qual By Similarity
- Qual Device P2DRV8870DDAR is qualified at MSL3 260C
- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-NPD-2204-019

#### **Qualification Report**

# DRV8870DDAR PCN bond-out spin at DMOS6 primary source | DMOS6 -> CD-BP -> FMX (TI Mexico) Approve Date 07-SEPTEMBER-2023

#### **Qualification Results**

#### Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Name	Condition	Duration	Qual Device: P1DRV8870DDAR	QBS Reference: TLV62569DBVR	QBS Reference: <u>DRV8251DDAR</u>
HAST	A2	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0
UHAST	A3	Autoclave	121C/15psig	96 Hours	-	3/231/0	3/231/0
TC	A4	Temperature Cycle	-65C/150C	500 Cycles	-	3/231/0	3/231/0
HTSL	A6	High Temperature Storage Life	150C	1000 Hours	-	3/231/0	3/231/0
HTOL	B1	Life Test	125C	1000 Hours	-	3/231/0	1/77/0
ELFR	B2	Early Life Failure Rate	125C	48 Hours	-	3/2400/0	-
SD	СЗ	PB Solderability	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes); PB Solder;	-	-	-	3/66/0
SD	C3	PB-Free Solderability	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes); PB-Free Solder;	-	-	-	3/66/0
ESD	E2	ESD CDM	-	1500 Volts	-	3/9/0	1/3/0
ESD	E2	ESD HBM	-	2000 Volts	-	3/9/0	1/3/0
ESD	E2	ESD HBM	-	4000 Volts	-	3/9/0	1/3/0
LU	E4	Latch-Up	Per JESD78	-	-	3/9/0	1/6/0

Туре	#	Test Name	Condition	Duration	Qual Device: P1DRV8870DDAR	QBS Reference: TLV62569DBVR	QBS Reference: DRV8251DDAR
CHAR	E5	Electrical Characterization	Min, Typ, Max Temp	-	1/30/0	3/90/0	3/90/0
CHAR	E5	Electrical Characterization	Per Datasheet Parameters	-	1/30/0	3/90/0	3/90/0

- QBS: Qual By Similarity
- Qual Device P1DRV8870DDAR is qualified at MSL3 260C
- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: <a href="http://www.ti.com/">http://www.ti.com/</a>

TI Qualification ID: R-NPD-2204-018

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.

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